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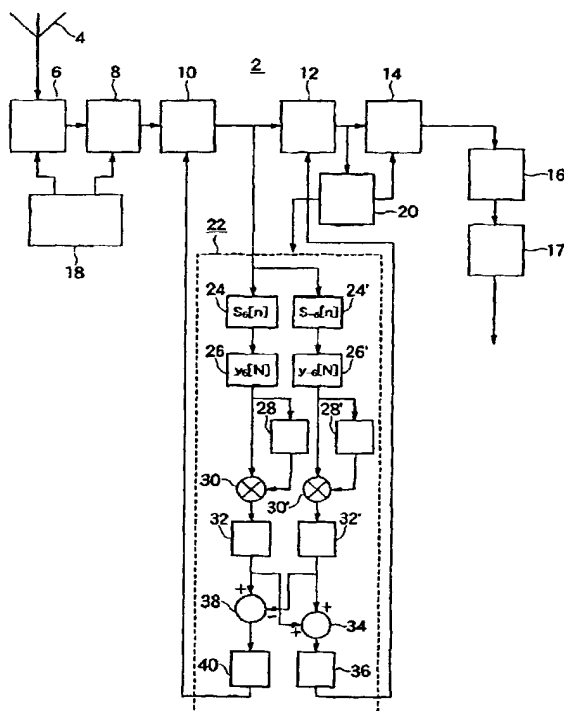
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(54) Title: COMPENSATION OF SAMPLING FREQUENCY OFFSET AND LOCAL OSCILLATOR FREQUENCY OFFSET IN A OFDM RECEIVER



(57) Abstract: A partial Fourier Transform is performed, using Goertzel's algorithm, to calculate two frequency bins. A phase variation is calculated for each bin, the phase variation preferably representing the phase difference between the bin calculated by a Fourier Transform performed on samples in a guard interval and the bin calculated by a Fourier Transform performed on matching samples within the useful part of the symbol. The local oscillator frequency offset is compensated by summing the phase variations, and the sampling frequency offset is compensated by taking the difference between the phase variations.

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